Supporting Information (SI) for Self-catalyst β -Ga₂O₃ semiconductor

lateral nanowire networks synthesis on the insulating substrate for

deep ultraviolet photodetectors

Yutong Wu^{a,b,} Shuanglong Feng^b, Miaomiao Zhang^{b,c}, Shuai Kang^b, Kun Zhang^{a,b}, Zhiyong Tao^d, Yaxian Fan^d*, and Wenqiang Lu^{b,c*}

 ^a Key Laboratory of In-Fiber Integrated Optics, Ministry Education of China, Harbin Engineering University, Harbin, 150001, PR China
^b Chongqing Key Laboratory of Multi-Scale Manufacturing Technology, Chongqing Institute of Green and Intelligent Technology, Chinese Academy of Sciences, Chongqing, 400714, PR China

^cChongqing College, University of Chinese Academy of Sciences, Chongqing, 400714, PR China

^d Guangxi Key Laboratory of Wireless Wideband Communication and Signal Processing, Guilin 541004, China

*Corresponding Authors: yxfan@guet.edu.cn;

1. Experimental setup of β -Ga₂O₃ NWs growth



Figure S1. Experimental setup of β -Ga₂O₃ NWs growth

2. The average diameter of the statistics nanowires



Figure S2. (a) SEM image; (b) histogram of the diameter of the statistics nanowires

3. TGA test for nanowire surface about ratio among organic vs inorganic.



Figure S3. TGA of $\beta\text{-}Ga_2O_3$ nanowires

4. SEM image of β -Ga₂O₃ nanowires at 20 minutes growth time.



Figure S4. SEM image of β -Ga₂O₃ nanowires at 20 minutes growth time (a) Large scope. (b) single nanowire enlarged view

5. Spectral response of photodetector



Figure S5. Spectral response of photodetector from 245 nm to 600 nm wavelength

6. Optical image of MSM β -Ga₂O₃ NWs photodetector device



Figure S6. MSM β -Ga₂O₃ NWs photodetector device